DATA SHEET



MOS FIELD EFFECT TRANSISTOR **3SK206**

RF AMP. FOR UHF TV TUNER N-CHANNEL GaAs DUAL GATE MES FIELD-EFFECT TRANSISTOR

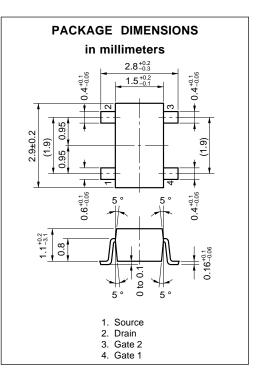
4PIN MINI MOLD

FEATURES

- Suitable for use as RF amplifier in UHF TV tuner.
- Low C_{rss}: 0.02 pF TYP.
- High GPS: 20 dB TYP.
- Low NF: 1.1 dB TYP.

ABSOLUTE MAXIMUM RATINGS (TA = $25 \degree$ C)

Drain to Source Voltage	Vdsx	10	V
Gate1 to Source Voltage	Vg1s	-4.5	V
Gate2 to Source Voltage	Vg2s	-4.5	V
Drain Current	lо	80	mA
Total Power Dissipation	P⊤	200	mW
Channel Temperature	T_{ch}	125	°C
Storage Temperature	Tstg	-55 to +125	°C



ELECTRICAL CHARACTERISTICS (TA = 25 $^{\circ}$ C)

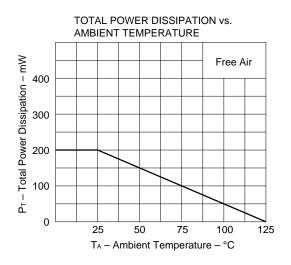
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Drain to Source Breakdown Voltage	BV _{DSX}	10			V	$V_{G1S} = -4 V$, $V_{G2S} = 0$, $I_D = 20 \mu A$	
Drain Current	IDSS	10		80	mA	$V_{DS} = 5 V, V_{G1S} = 0, V_{G2S} = 0$	
Gate1 to Source Cutoff Voltage	VG1S(off)			-3.5	V	$V_{DS} = 5 V, V_{G2S} = 0, I_D = 100 \mu A$	
Gate2 to Source Cutoff Voltage	VG2S(off)			-3.5	V	$V_{DS} = 5 V, V_{G1S} = 0, I_D = 100 \mu A$	
Gate1 Reverse Current	I _{G1SS}			10	μΑ	$V_{DS} = 0, V_{G1S} = -4 V, V_{G2S} = 0$	
Gate2 Reverse Current	lg2ss			10	μΑ	$V_{DS} = 0, V_{G2S} = -4 V, V_{G1S} = 0$	
Forward Transfer Admittance	y _{fs}	25	35		mS	$V_{DS} = 5 V, V_{G2S} = 1 V, I_D = 10 mA, f = 1.0 kHz$	
Input Capacitance	Ciss	1.0	1.5	2.0	pF	Vds = 5 V, Vg2s = 1 V, Id = 10 mA,	
Reverse Transfer Capacitance	Crss		0.02	0.035	pF	f = 1.0 MHz	
Power Gain	Gps	16.0	20.0		dB	$V_{DS} = 5 V$, $V_{G2S} = 1 V$, $I_D = 10 mA$,	
Noise Figure	NF		1.1	2.5	dB	f = 900 MHz	

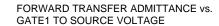
IDSS Classification (Unit: mA)

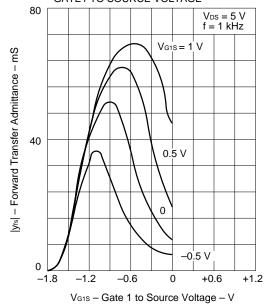
Class	U76	U77	U78	U79
Marking	U76	U77	U78	U79
loss	10 to 25	20 to 35	30 to 50	45 to 80

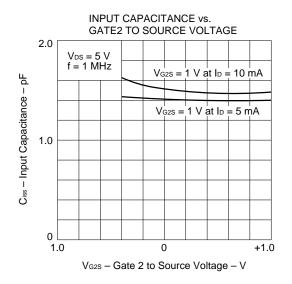
PRECAUTION: Avoid high static voltages or electric fields so that this device would not suffer from any damage due to those voltage or fields.

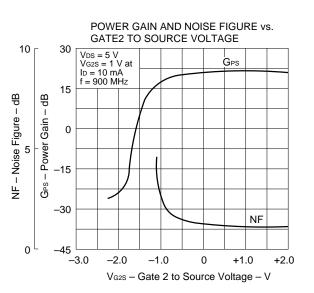
TYPICAL CHARACTERISTICS (T_A = 25 $^{\circ}$ C)



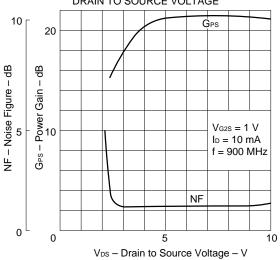




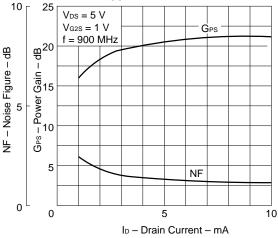


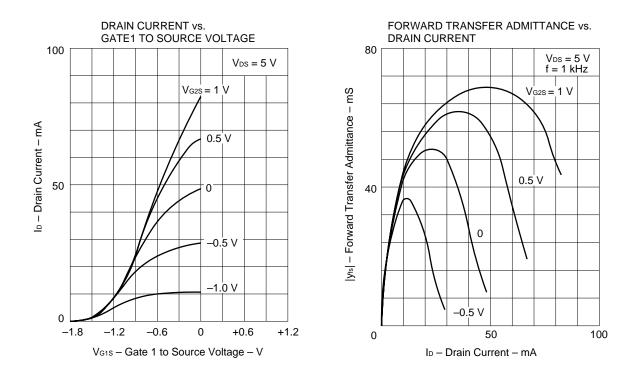


POWER GAIN AND NOISE FIGURE vs. DRAIN TO SOURCE VOLTAGE



POWER GAIN AND NOISE FIGURE vs. DRAIN CURRENT

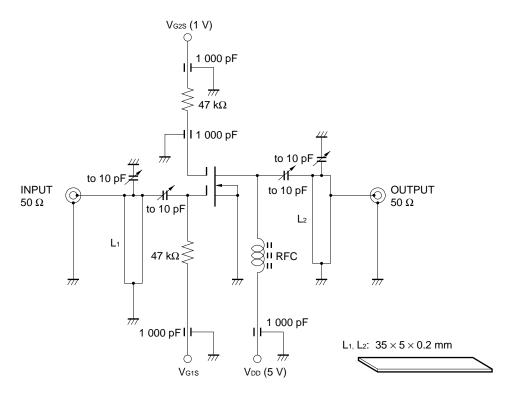




S-PARAMETER (VDS = 5 V, VG2S = 1 V, ID = 10 mA)

FREQUENCY	5	S11	S	21	S	S 12	S	22
(MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.00	1.003	-4.9	3.938	175.0	0.004	41.9	0.963	-1.5
200.00	0.984	-11.9	4.009	164.1	0.001	-173.5	0.958	-4.2
300.00	0.985	-14.9	3.859	158.5	0.006	71.7	0.972	-4.8
400.00	0.964	-21.8	3.766	151.3	0.005	93.9	0.972	-8.2
500.00	0.928	-24.6	3.699	149.1	0.005	74.5	0.965	-8.6
600.00	0.928	-31.9	3.886	138.8	0.008	84.2	0.983	-13.1
700.00	0.869	-33.5	3.612	132.3	0.003	65.8	0.961	-12.1
800.00	0.889	-39.8	3.643	126.1	0.004	98.0	0.995	-16.2
900.00	0.832	-42.9	3.553	121.5	0.004	102.4	0.981	-17.0
1000.00	0.847	-47.1	3.817	115.2	0.003	-173.4	1.039	-20.8
1100.00	0.795	-49.8	3.681	106.1	0.010	-155.7	0.999	-22.3
1200.00	0.833	-51.4	3.747	100.4	0.021	-147.3	1.107	-25.1

900 MHz GPS AND NF TEST CIRCUIT



 $V_{DS} = 5 V$, $V_{G2S} = 1 V$, $I_D = 10 mA$

[MEMO]

[MEMO]

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Anti-radioactive design is not implemented in this product.

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